



30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
30V	1.5Ω @ V _{GS} = 4.5V	0.41A
	2.0Ω @ V _G S = 2.5V	0.35A
	3.0Ω @ $V_{GS} = 1.8V$	0.29A
	4.5Ω @ V _G S = 1.5V	0.23A

Features and Benefits

- Low Package Profile
- 0.6mm × 0.4mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Mechanical Data

- Case: X2-DFN0604-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (Approximate)

X2-DFN0604-3

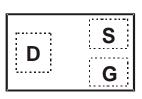


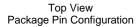


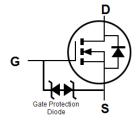
Top View



Bottom View







Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN31D5UFO-7B	X2-DFN0604-3	10k/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Top View Bar Denotes Gate and Source Side

DC = Product Type Marking Code



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			Vgss	±12	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V Steady T _A = +25°C T _A = +85°C		lo	0.41 0.32	А	
Pulsed Drain Current (Note 6)			I _{DM}	0.7	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P _D	0.38	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	332	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

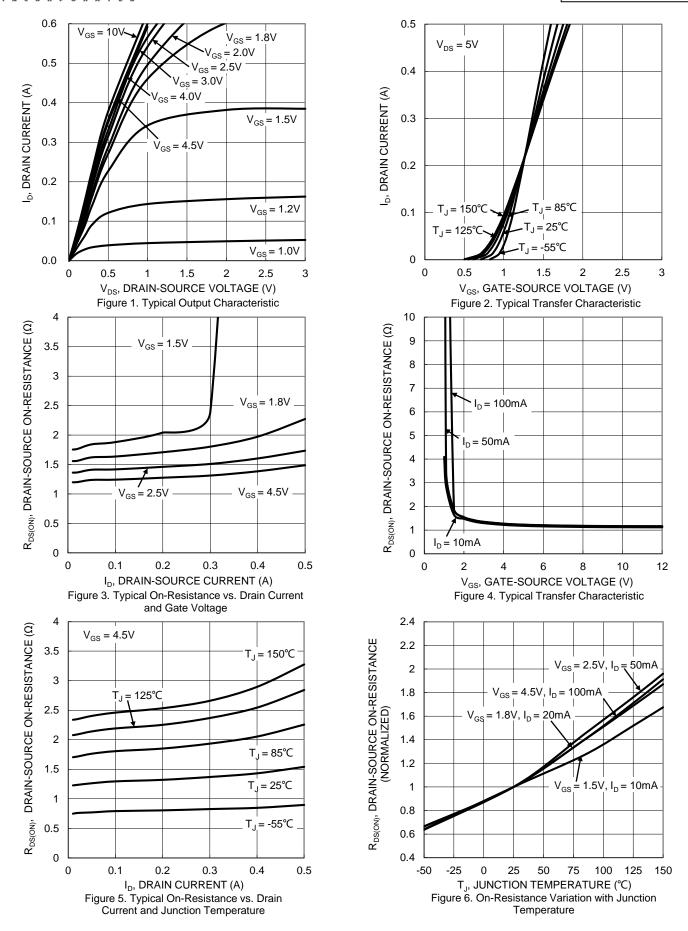
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	,			ı			
Drain-Source Breakdown Voltage	BVDSS	30	_	_	V	V _G S = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	IDSS	_	_	100	μA	V _{DS} = 24V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	<u> </u>						
Gate Threshold Voltage	V _{GS(TH)}	0.4	_	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	1.2	1.5		V _G S = 4.5V, I _D = 100mA	
Static Drain-Source On-Resistance	D	_	1.4	2.0	Ω	Vgs = 2.5V, ID = 50mA	
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	1.6	3.0		$V_{GS} = 1.8V, I_D = 20mA$	
		_	1.8	4.5		V _G S = 1.5V, I _D = 10mA	
Diode Forward Voltage	VsD	_	0.6	1.0	V	Vgs = 0V, Is = 10mA	
DYNAMIC CHARACTERISTICS (Note 8)	<u> </u>						
Input Capacitance	Ciss	_	22.6	_	pF	15)/)/ 0)/	
Output Capacitance	Coss	_	2.68	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ $V_{DS} = 1.0MHz$	
Reverse Transfer Capacitance	Crss	_	1.8	_	pF	1 - 1.01411 12	
Total Gate Charge	Qg	_	0.38	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Qgs	_	0.05	_	nC	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 200mA	
Gate-Drain Charge	Q _{gd}	_	0.07	_	nC	- ID = 200MA	
Turn-On Delay Time	t _{D(ON)}	_	3.2	_	ns		
Turn-On Rise Time	t _R	_	2.2	_	ns	V _{DD} = 15V, V _{GS} = 4.5V,	
Turn-Off Delay Time	t _{D(OFF)}	_	21	_	ns	$R_G = 2\Omega$, $I_D = 200mA$	
Turn-Off Fall Time	tF	_	7.5	_	ns	7	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







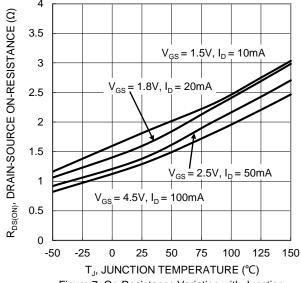


Figure 7. On-Resistance Variation with Junction Temperature

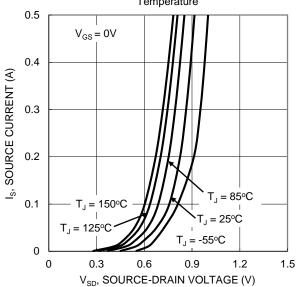


Figure 9. Diode Forward Voltage vs. Current

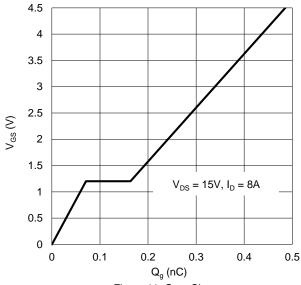


Figure 11. Gate Charge

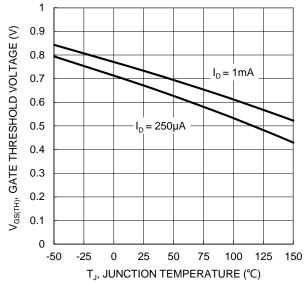
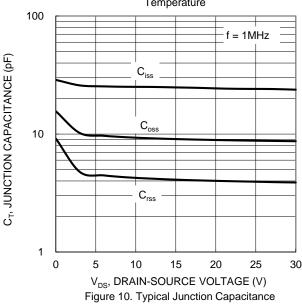


Figure 8. Gate Threshold Variation vs. Junction Temperature



Limited DRAIN CURRENT (A) 0.1 = 10ms 1s 0.01 $T_{J(Max)} = 150^{\circ}C$ $T_C = 25^{\circ}C$ مْ_ Single Pulse DUT on 1*MRP Board $V_{GS} = 4.5V$ 0.001 0.1 10 100 V_{DS} , DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



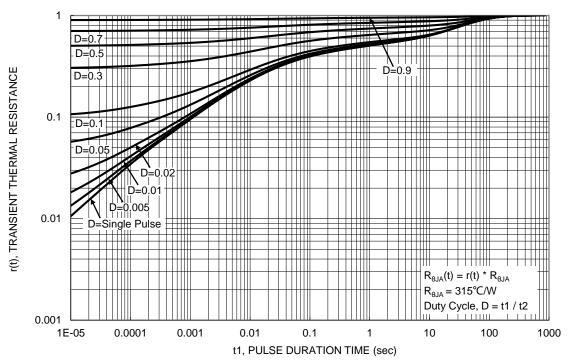


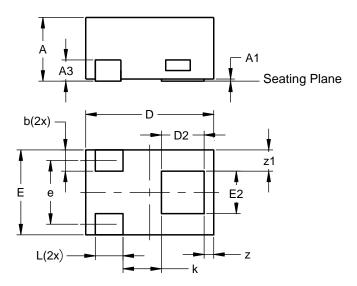
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3

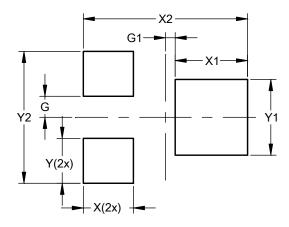


X2-DFN0604-3					
Dim	Min	Max	Тур		
Α		0.40	0.36		
A 1	0.00	0.03	0.02		
А3	-		0.10		
b	0.07	0.15	0.10		
D	0.55	0.65	0.60		
D2	0.15	0.25	0.20		
Е	0.35	0.45	0.40		
E2	0.15	0.25	0.20		
e			0.30		
k	0.15				
L	0.10	0.18	0.13		
Z			0.045		
z1			0.10		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3



Dimensions	Value (in mm)
G	0.075
G1	0.035
Х	0.180
X1	0.260
X2	0.590
Y	0.160
Y1	0.270
Y2	0.470



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